

NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **ASI MRF553** is designed for Low power amplifier applications.

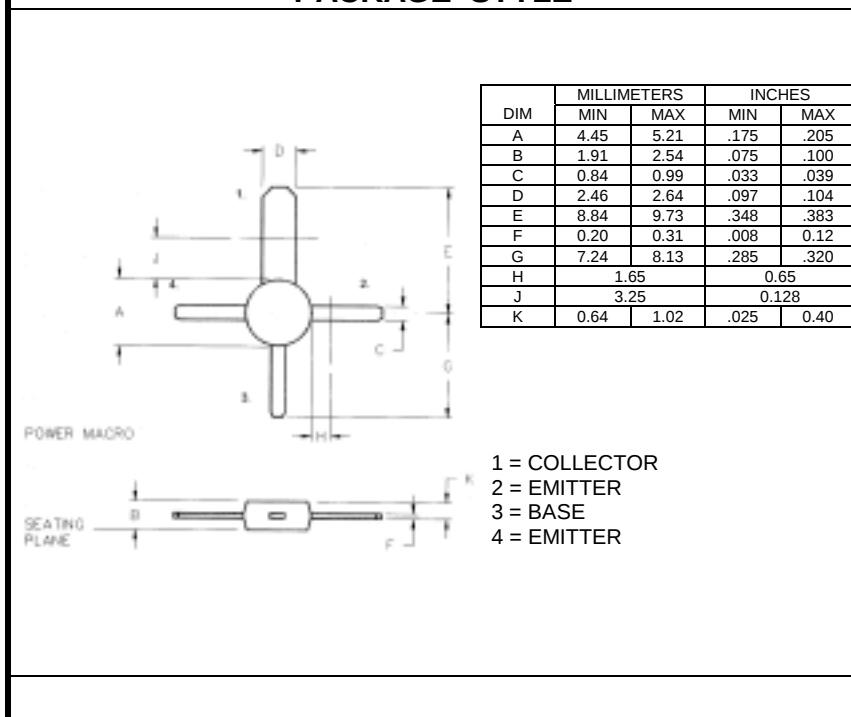
FEATURES:

- 12.5 V, 175 MHz.
- $P_{OUT} = 1.5\text{ W}$
- $G_P = 11.5\text{ min.}$
- $\eta = 60\%$ (Typ)

MAXIMUM RATINGS

I_C	500 mA
V_{CB}	36 V
P_{DISS}	3.0 W @ $T_C = 75^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	41.7 $^\circ\text{C/W}$

PACKAGE STYLE



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$	16			V
BV_{CBO}	$I_C = 5.0\text{ mA}$	36			V
BV_{CES}	$I_C = 5.0\text{ mA}$	36			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	4.0			V
I_{CES}	$V_{CE} = 15\text{ V}$			5.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 250\text{ mA}$	30		200	---
C_{CB}	$V_{CB} = 10\text{ V}$ $f = 1.0\text{ MHz}$		12	20	pF
G_{PE}	$V_{CE} = 12\text{ V}$ $P_{OUT} = 1.5\text{ W}$ $f = 175\text{ MHz}$	11.5	13		dB
η		50	60		%
ψ		10:1			---